

**OCTAL D-TYPE LATCH WITH 3-STATE OUTPUT**  
**TC74AC373P/F/FW NON-INVERTING**  
**TC74AC533P/F/FW INVERTING**

The TC74AC373 and TC74AC533 are advanced high speed CMOS OCTAL LATCH with 3-STATE OUTPUT fabricated with silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology.

They achieve the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

These 8-bit D-type latches are controlled by a latch enable input (LE) and a output enable input ( $\overline{OE}$ ).

When the  $\overline{OE}$  input is high, the eight outputs are in a high impedance state.

The TC74AC373 has non-inverting outputs, and TC74AC533 has inverting outputs.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

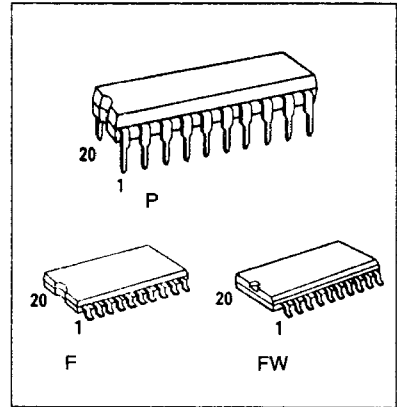
**FEATURES:**

- High Speed .....  $t_{pd}=4.8$  ns(typ.) at  $V_{CC}=5V$
- Low Power Dissipation .....  $I_{CC}=8\mu A$ (Max.) at  $T_a=25^\circ C$
- High Noise Immunity .....  $V_{NIH}=V_{NIL}=28\% V_{CC}$ (Min.)
- Symmetrical Output Impedance .....  $|I_{OH}|=I_{OL}=24mA$ (Min.)  
 Capability of driving  $50\Omega$  transmission lines.
- Balanced Propagation Delays .....  $t_{PLH}\approx t_{PHL}$
- Wide Operating Voltage Range ...  $V_{CC}(opr)=2V\sim 5.5V$
- Pin and Function Compatible with 74F 373/533

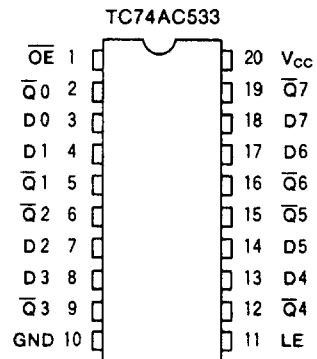
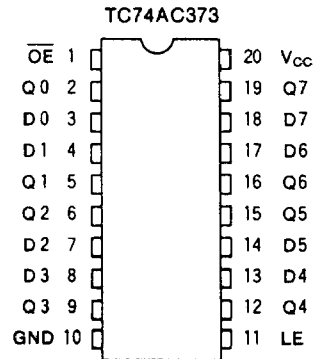
**TRUTH TABLE**

INPUTS			OUTPUTS	
$\overline{OE}$	LE	D	Q(373)	$\overline{Q}$ (533)
H	X	X	Z	Z
L	L	X	$Q_n$	$\overline{Q}_n$
L	H	L	L	H
L	H	H	H	L

X : Don't Care  
 Z : High Impedance  
 $Q_n(Q_n)$  : Q (Q) outputs are latched at the time when the LE input is taken to a low logic level.



**PIN ASSIGNMENT (TOP VIEW)**



TC74AC373,533P/F/FW-1

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	$V_{CC}$	-0.5 ~ 7.0	V
DC Input Voltage	$V_{IN}$	-0.5 ~ $V_{CC}+0.5$	V
DC Output Voltage	$V_{OUT}$	-0.5 ~ $V_{CC}+0.5$	V
Input Diode Current	$I_{IK}$	±20	mA
Output Diode Current	$I_{OK}$	±50	mA
DC Output Current	$I_{OUT}$	±50	mA
DC $V_{CC}$ /Ground Current	$I_{CC}$	±200	mA
Power Dissipation	$P_D$	500(DIP)* / 180(SOP)	mW
Storage Temperature	$T_{stg}$	-65 ~ 150	°C
Lead Temperature 10sec	$T_L$	300	°C

\*500mW in the range of  $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$ . From  $T_a = 65^{\circ}\text{C}$  to  $85^{\circ}\text{C}$  a derating factor of -10mW/°C should be applied up to 300mW.

### RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	$V_{CC}$	2.0 ~ 5.5	V
Input Voltage	$V_{IN}$	0 ~ $V_{CC}$	V
Output Voltage	$V_{OUT}$	0 ~ $V_{CC}$	V
Operating Temperature	$T_{opr}$	-40 ~ 85	°C
Input Rise and Fall Time	dt/dv	0 ~ 100 ( $V_{CC} = 3.3 \pm 0.3\text{V}$ ) 0 ~ 20 ( $V_{CC} = 5 \pm 0.5\text{V}$ )	ns/v

### DC ELECTRICAL CHARACTERISTICS

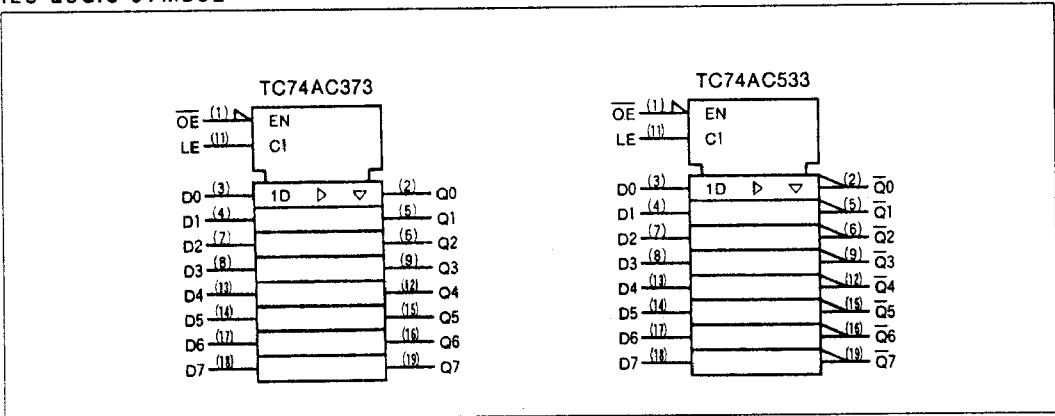
PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}$	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High-Level Input Voltage	$V_{IH}$		2.0	1.50	-	-	1.50	-	V	
			3.0	2.10	-	-	2.10	-		
			5.5	3.85	-	-	3.85	-		
Low-Level Input Voltage	$V_{IL}$		2.0	-	-	0.50	-	0.50	V	
			3.0	-	-	0.90	-	0.90		
			5.5	-	-	1.65	-	1.65		
High-Level Output Voltage	$V_{OH}$	$V_{IN} =$ $V_{IH}$ or $V_{IL}$	$I_{OH} = -50\mu\text{A}$	2.0	1.9	2.0	-	1.9	-	V
				3.0	2.9	3.0	-	2.9	-	
				4.5	4.4	4.5	-	4.4	-	
		$I_{OH} = -4\text{mA}$ $I_{OH} = -24\text{mA}$ $I_{OH} = -75\text{mA}^*$	3.0	2.58	-	-	2.48	-		
			4.5	3.94	-	-	3.80	-		
			5.5	-	-	-	3.85	-		
Low-Level Output Voltage	$V_{OL}$	$V_{IN} =$ $V_{IH}$ or $V_{IL}$	$I_{OL} = 50\mu\text{A}$	2.0	-	0.0	0.1	-	0.1	V
				3.0	-	0.0	0.1	-	0.1	
				4.5	-	0.0	0.1	-	0.1	
		$I_{OL} = 12\text{mA}$ $I_{OL} = 24\text{mA}$ $I_{OL} = 75\text{mA}^*$	3.0	-	-	0.36	-	0.44		
			4.5	-	-	0.36	-	0.44		
			5.5	-	-	-	-	1.65		
3-State Output Off-State Current	$I_{OZ}$	$V_{IN} = V_{IH}$ or $V_{IL}$ $V_{OUT} = V_{CC}$ or GND	5.5	-	-	±0.5	-	±5.0	$\mu\text{A}$	
Input Leakage Current	$I_{IN}$	$V_{IN} = V_{CC}$ or GND	5.5	-	-	±0.1	-	±1.0		
Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND	5.5	-	-	8.0	-	80.0		

\*: This spec indicates the capability of driving 50Ω transmission lines.

One output should be tested at a time for a 10ms maximum duration.

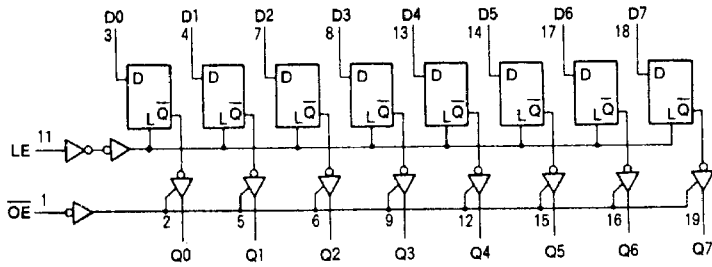
TC74AC373,533P/F/FW-2

IEC LOGIC SYMBOL

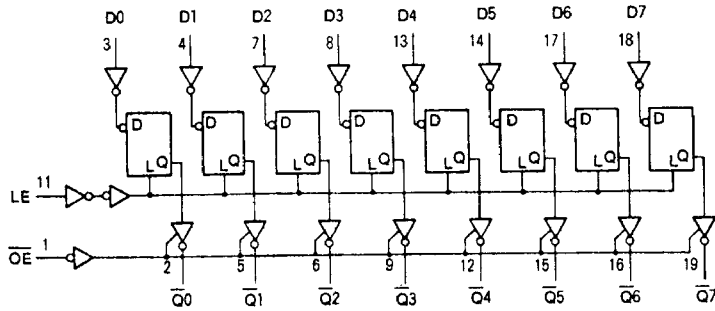


SYSTEM DIAGRAM

TC74AC373



TC74AC533



TC74AC373,533P/F/FW-3

**TIMING REQUIREMENTS (Input  $t_r=t_f=3ns$ )**

PARAMETER	SYMBOL	TEST CONDITION	Ta=25°C			Ta=-40~85°C	UNIT
			V <sub>CC</sub>	TYP.	LIMIT	LIMIT	
Minimum Pulse Width (LE)	$t_{W(H)}$		3.3±0.3	-	7.0	7.0	ns
			5.0±0.5	-	5.0	5.0	
Minimum Set-up Time	$t_s$		3.3±0.3	-	6.0	6.0	
			5.0±0.5	-	3.5	3.5	
Minimum Hold Time	$t_h$		3.3±0.3	-	1.0	1.0	
			5.0±0.5	-	1.0	1.0	

**AC ELECTRICAL CHARACTERISTICS (C<sub>L</sub>=50pF, R<sub>L</sub>=500Ω, Input  $t_r=t_f=3ns$ )**

PARAMETER	SYMBOL	TEST CONDITION	Ta=25°C			Ta=-40 ~85°C		UNIT	
			V <sub>CC</sub>	MIN.	TYP.	MAX.	MIN.		MAX.
Propagation Delay Time (LE-Q, Q)	$t_{pLH}$ $t_{pHL}$		3.3±0.3	-	7.7	13.2	1.0	15.0	ns
			5.0±0.5	-	6.1	8.7	1.0	10.0	
Propagation Delay Time (Dn-Q, Q)	$t_{pLH}$ $t_{pHL}$		3.3±0.3	-	7.6	12.9	1.0	14.7	
			5.0±0.5	-	5.8	8.3	1.0	9.5	
Output Enable Time	$t_{pZL}$ $t_{pZH}$		3.3±0.3	-	7.6	12.9	1.0	14.7	
			5.0±0.5	-	6.1	8.7	1.0	10.0	
Output Disable Time	$t_{pLZ}$ $t_{pHZ}$		3.3±0.3	-	7.0	11.0	1.0	12.5	
			5.0±0.5	-	5.4	7.5	1.0	8.5	
Input Capacitance	C <sub>IN</sub>		-	5	10	-	10	pF	
Output Capacitance	C <sub>OUT</sub>		-	10	-	-	-		
Power Dissipation Capacitance	C <sub>PD(1)</sub>		-	26	-	-	-		

Note(1) C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC(OP)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8(\text{per Latch})$$

And the total C<sub>PD</sub> when n pcs. of Latch operate can be gained by the following equation:

$$C_{PD}(\text{total}) = 26 + 12 \cdot n$$